

TENTATIVE

TOSHIBA INTEGRATED IGBT MODULE SILICON N CHANNEL IGBT

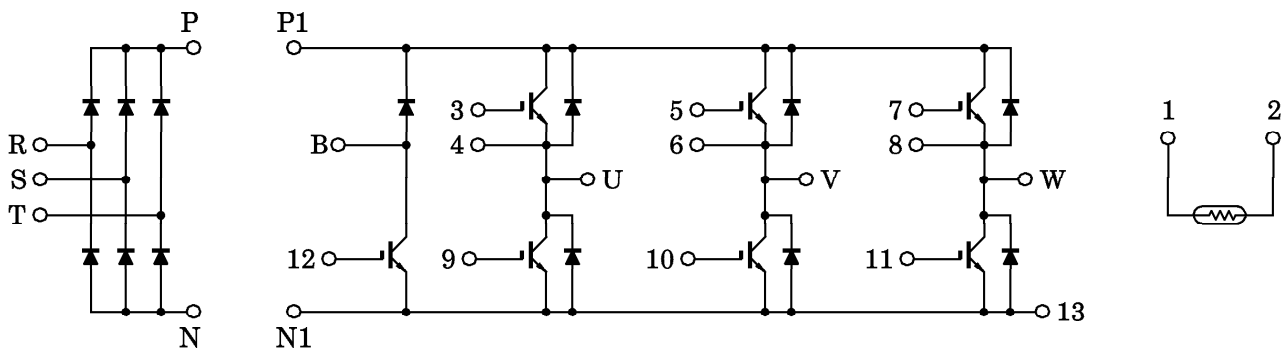
MIG20J906H, MIG20J906HA

HIGH POWER SWITCHING APPLICATIONS

MOTOR CONTROL APPLICATIONS

- Integrates Inverter, Converter and Brake Power Circuits and Thermistor in One Package.
- Output (Inverter Stage)
: 3 ϕ 20A/600V IGBT
- Input (Converter Stage)
: 3 ϕ 30A/800V Silicon Rectifier
- The Electrodes are Isolated from Case.
- Outline
MIG20J906H : 2-108E5A
MIG20J906HA : 2-108E6A
- Weight : 190g

EQUIVALENT CIRCUIT



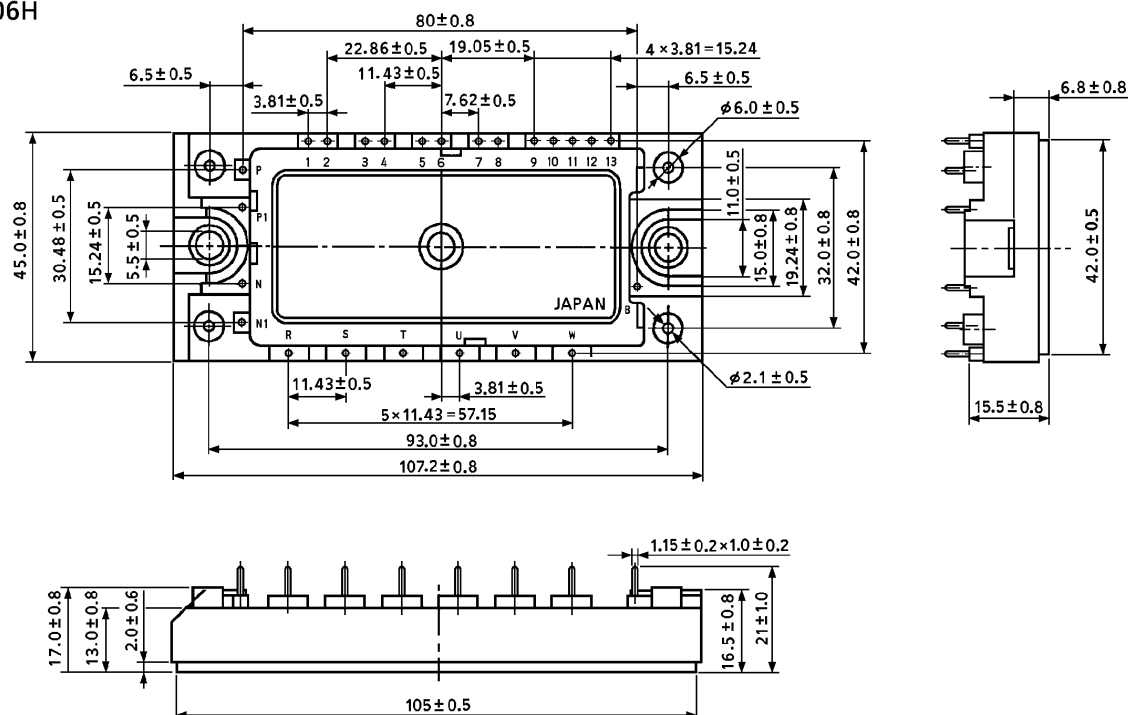
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Package Dimension

Unit : mm

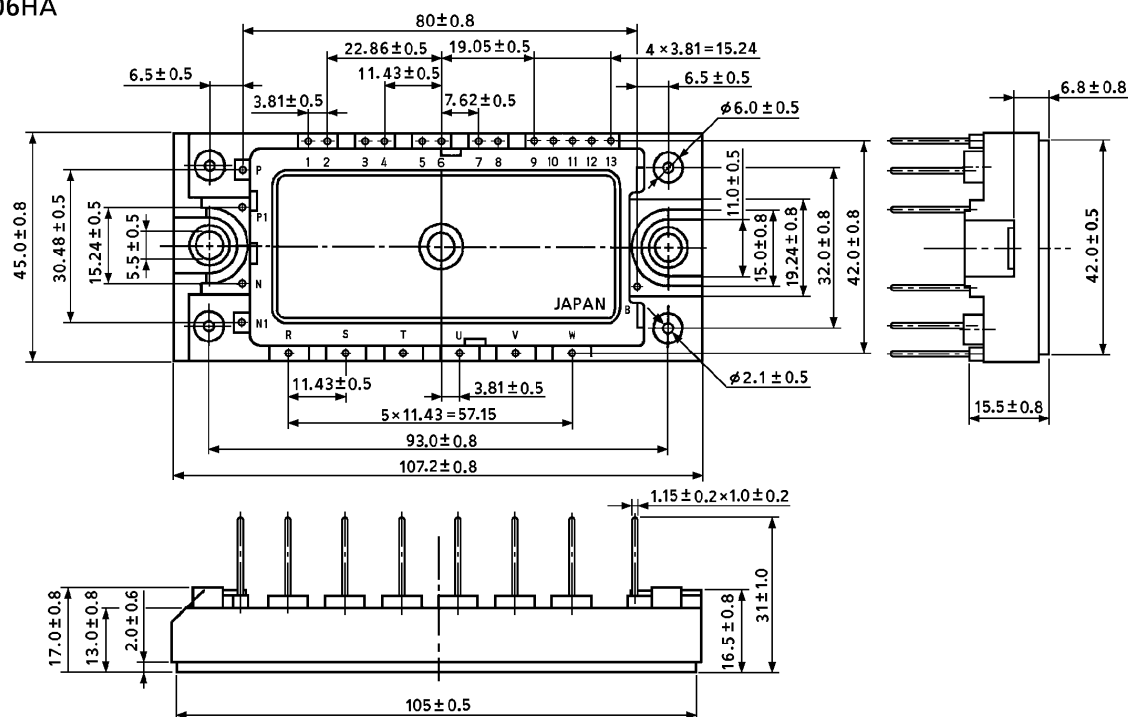
MIG20J906H



2-108E5A

Unit : mm

MIG20J906HA



2-108E6A

MAXIMUM RATINGS (Ta = 25°C)

STAGE		CHARACTERISTIC		SYMBOL	RATING	UNIT	
Inverter		Collector-Emitter Voltage		V _{CES}	600	V	(25°C / 40°C) (25°C / 40°C)
		Gate-Emitter Voltage		V _{GES}	± 20	V	
		Collector Current	DC	I _C	25 / 20	A	
			1ms	I _{CP}	50 / 40	A	
		Forward Current	DC	I _F	20	A	
			1ms	I _{FM}	40	A	
Collector Power Dissipation (T _c =25°C)		P _C	90	W			
Converter		Repetitive Peak Reverse Voltage		V _{RRM}	800	V	
		Average Output Rectified Current		I _O	30	A	
		Peak One Cycle Surge Forward Current (50Hz, Non-Repetitive)		I _{FSM}	400	A	
Brake	IGBT	Collector-Emitter Voltage		V _{CES}	600	V	(25°C / 40°C) (25°C / 40°C)
		Gate-Emitter Voltage		V _{GES}	± 20	V	
		Collector Current	DC	I _C	25 / 20	A	
			1ms	I _{CP}	50 / 40	A	
	Collector Power Dissipation (T _c =25°C)		P _C	90	W		
	FWD	Reverse Voltage		V _R	600	V	
		Forward Current	DC	I _F	20	A	
			1ms	I _{FM}	40	A	
Module		Junction Temperature		T _j	150	°C	
		Storage Temperature Range		T _{stg}	−40~125	°C	
		Isolation Voltage		V _{Isol}	2500 (AC 1 minute)	V	
		Screw Torque		—	6	N·m	

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

a. Inverter stage

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	± 500	nA
Collector Cut-Off Current		I_{CES}	$V_{CE} = 600V, V_{GE} = 0$	—	—	1.0	mA
Gate-Emitter Cut-Off Voltage		$V_{GE} (off)$	$I_C = 2mA, V_{CE} = 5V$	5.0	—	8.0	V
Collector-Emitter Saturation Voltage		$V_{CE} (sat)$	$I_C = 20A$ $V_{GE} = 15V$	—	2.1	2.7	V
			$T_j = 25^\circ C$ $T_j = 125^\circ C$	—	2.2	2.8	
Input Capacitance		C_{ies}	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	1850	—	pF
Switching Time	Rise Time	t_r	$V_{CC} = 300V$ $I_C = 20A$ $V_{GE} = \pm 15V$ $R_G = 62\Omega$ (Note 1)	—	0.10	0.20	μs
	Turn-On Time	t_{on}		—	0.25	0.50	
	Fall Time	t_f		—	0.15	0.30	
	Turn-Off Time	t_{off}		—	0.50	0.80	
Forward Voltage		V_F	$I_F = 20A, V_{GE} = 0$	—	2.0	2.8	V
Reverse Recovery Time		t_{rr}	$I_F = 20A, V_{GE} = -10V,$ $di/dt = 100A/\mu s$	—	0.08	0.15	μs
Thermal Resistance		$R_{th(j-c)}$	Transistor	—	—	1.39	$^\circ C/W$
			Diode	—	—	2.6	

b. Converter stage

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM} = 800V$	—	—	50	μA
Peak Forward Voltage	V_{FM}	$I_{FM} = 30A$	—	1.05	1.20	V
Peak One Cycle Surge Forward Current	I_{FSM}	50Hz sine-half-wave	400	—	—	A
Thermal Resistance	$R_{th(j-c)}$	—	—	—	1.56	$^\circ C/W$

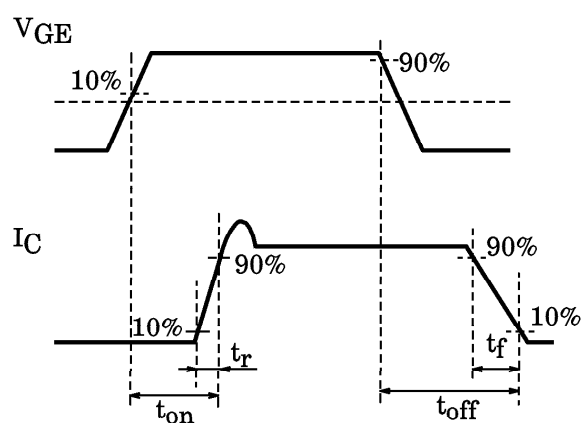
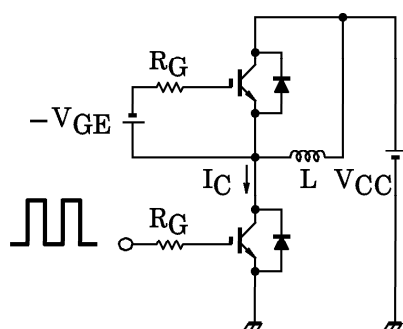
c. Brake stage

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	± 500	nA
Collector Cut-Off Current		I_{CES}	$V_{CE} = 600V, V_{GE} = 0$	—	—	1.0	mA
Reverse Current		I_R	$V_R = 600V$	—	—	1.0	mA
Gate-Emmitter Cut-Off Voltage		$V_{GE} (off)$	$I_C = 2mA, V_{CE} = 5V$	5.0	—	8.0	V
Collector-Emmitter Saturation Voltage		$V_{CE} (sat)$	$I_C = 20A$ $V_{GE} = 15V$	—	2.1	2.7	V
			$T_j = 25^\circ C$ $T_j = 125^\circ C$	—	2.2	2.8	
Input Capacitance		C_{ies}	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	1850	—	pF
Switching Time	Rise Time	t_r	$V_{CC} = 600V$ $I_C = 20A$ $V_{GE} = \pm 15V$ $R_G = 62\Omega$ (Note 1)	—	0.10	0.20	μs
	Turn-On Time	t_{on}		—	0.25	0.50	
	Fall Time	t_f		—	0.15	0.30	
	Turn-Off Time	t_{off}		—	0.50	0.80	
Forward Voltage		V_F	$I_F = 20A, V_{GE} = 0$	—	2.0	2.8	V
Thermal Resistance		$R_{th(j-c)}$	Transistor	—	—	1.39	$^\circ C / W$
			Diode	—	—	2.6	

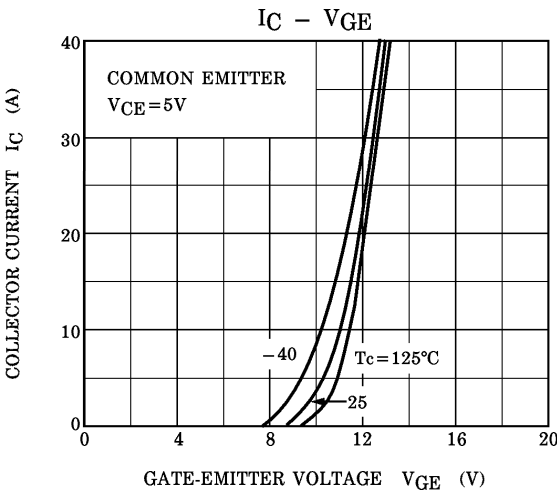
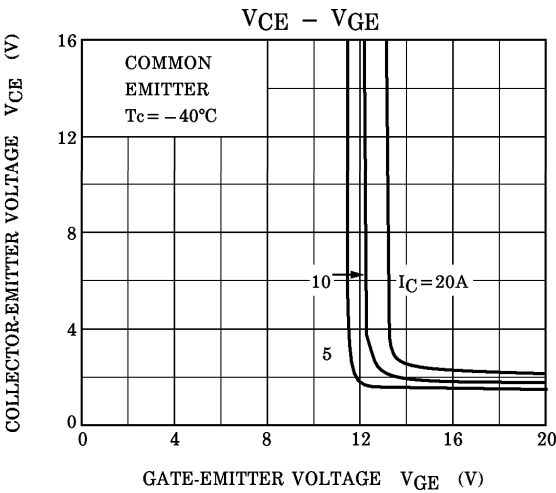
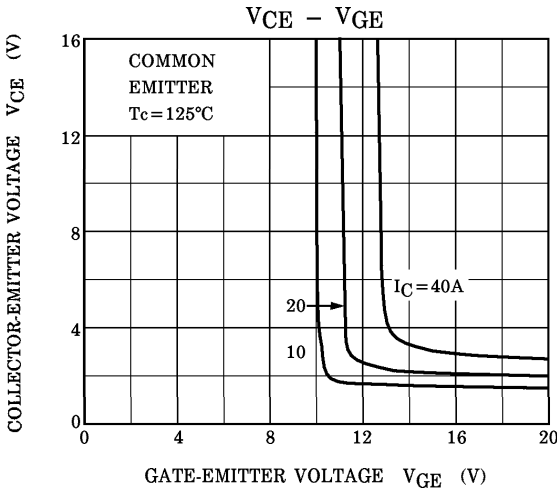
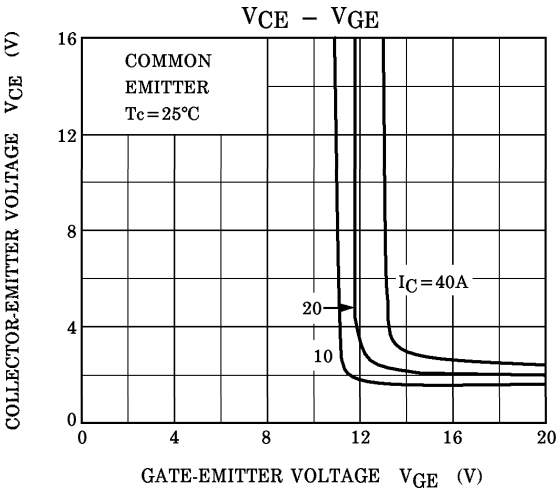
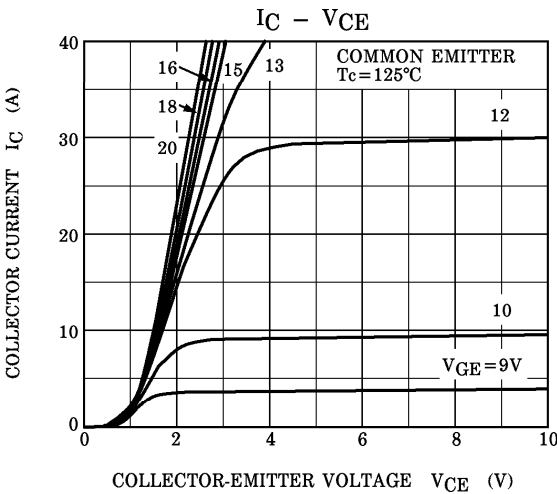
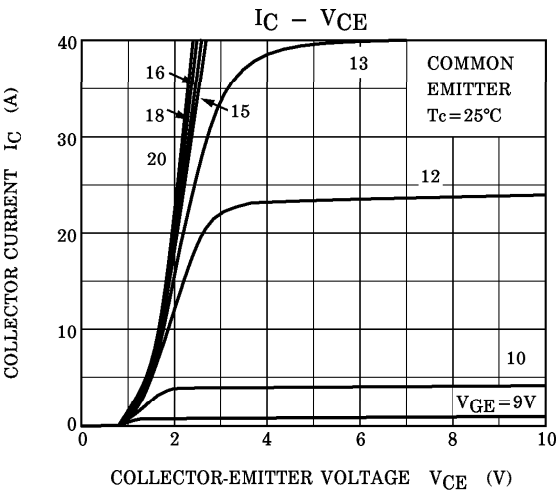
d. Thermistor

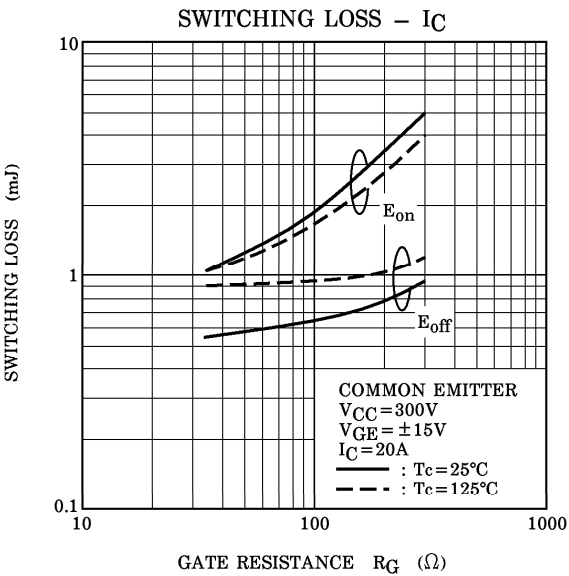
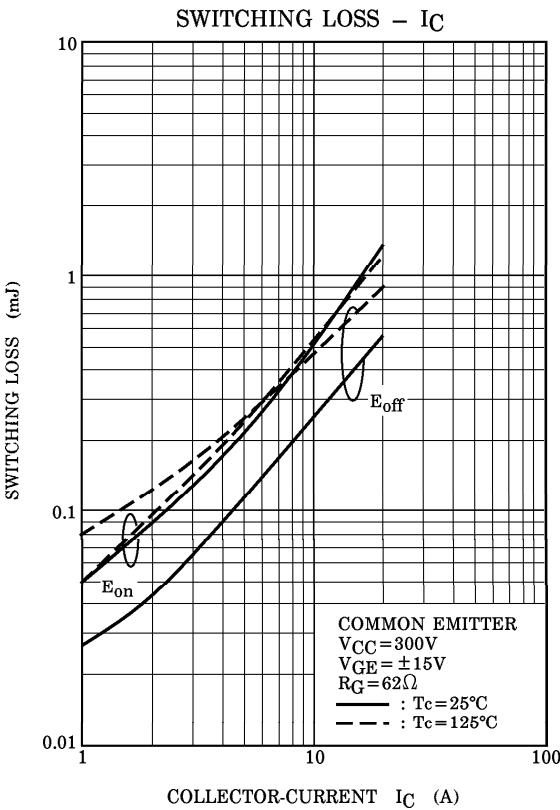
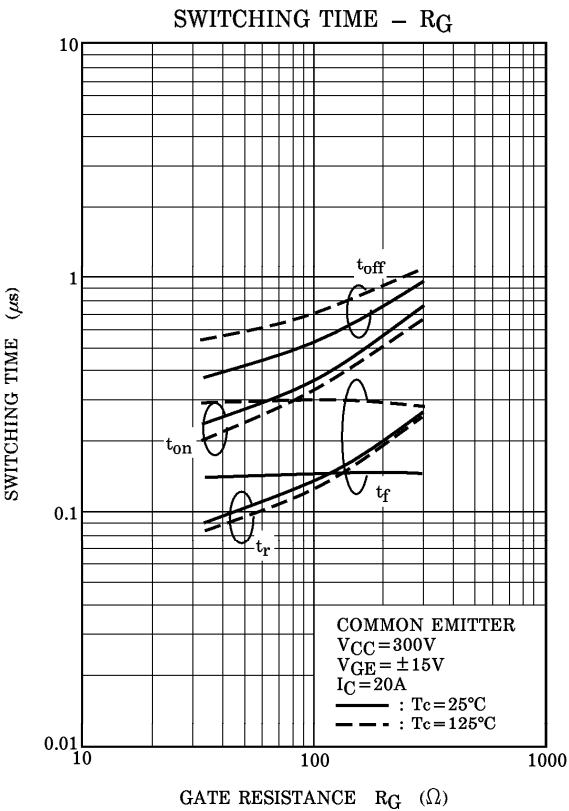
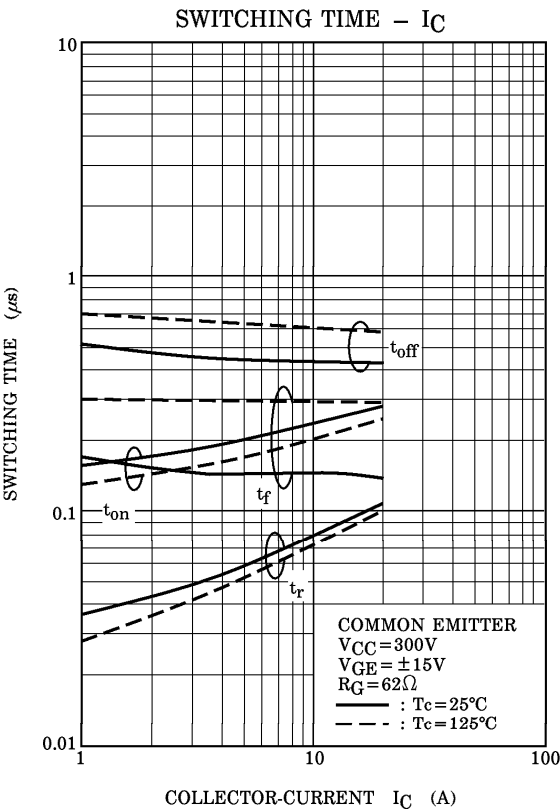
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Zero-power Resistance	R_{25}	$I_{TM} = 0.2mA, T_c = 25^\circ C$	17.31	20	23.14	$k\Omega$
B Value	$B_{25/85}$	$T_c = 25^\circ C / T_c = 85^\circ C$	—	3760	—	K

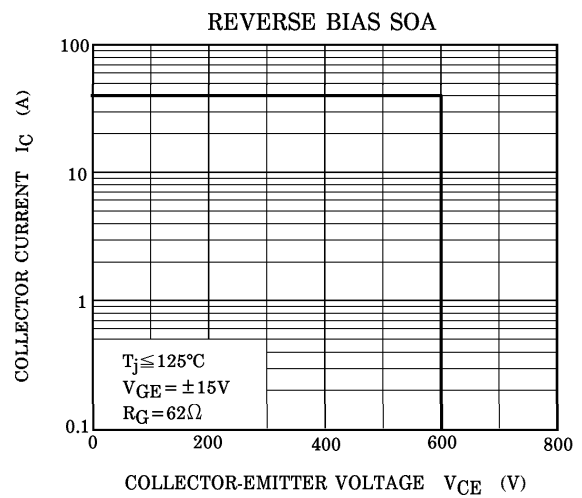
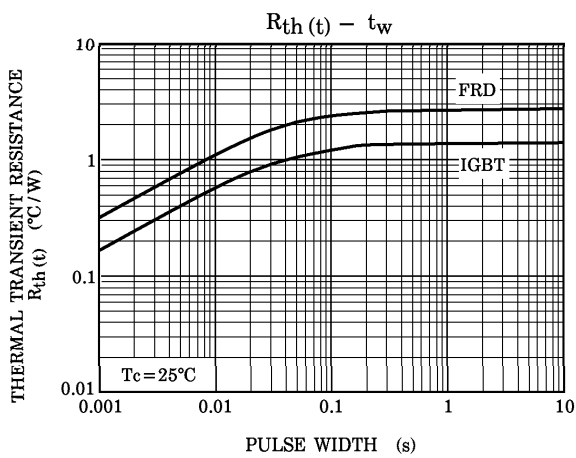
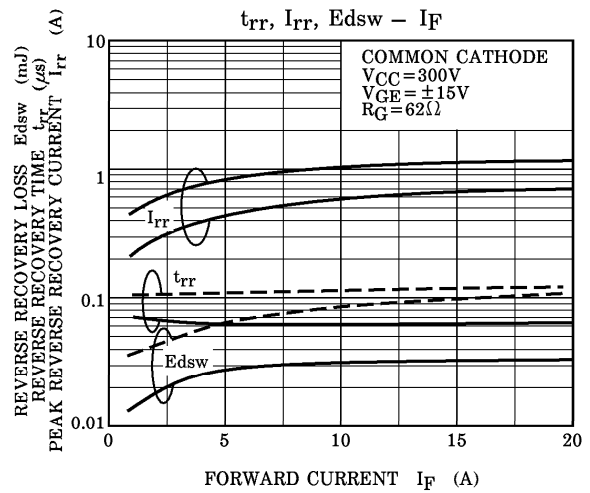
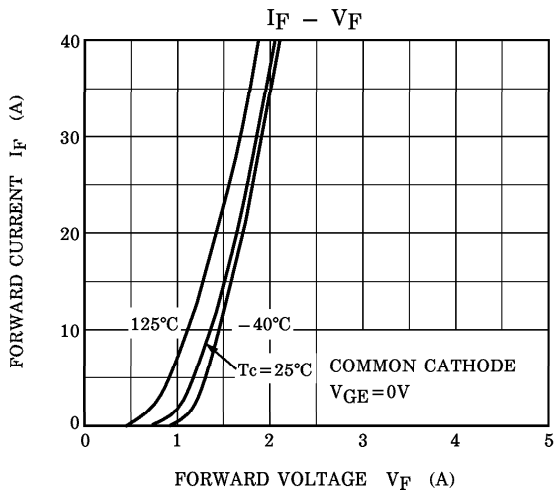
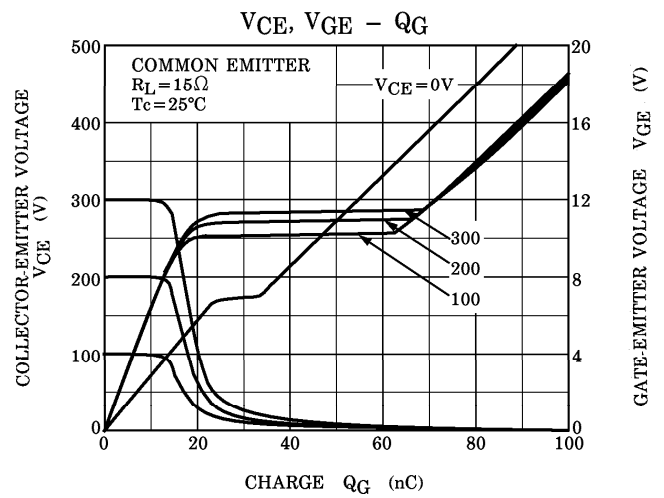
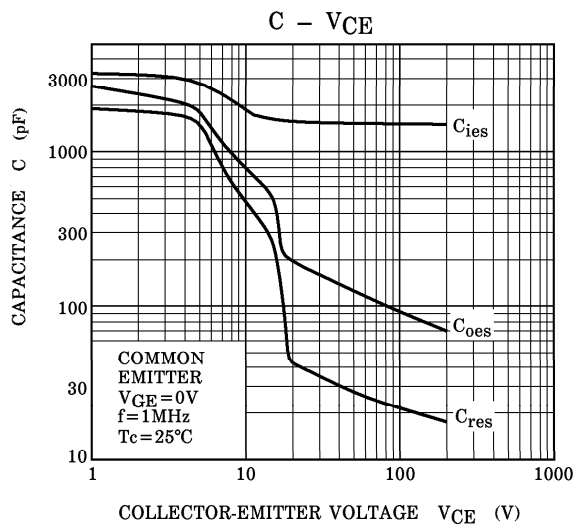
(Note 1) Switching Time Test Circuit & Timing Chart



a. Inverter stage / c. Brake stage







b. Converter stage

